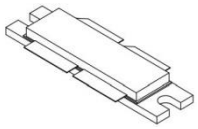
MQ081K0VP LDMOS TRANSISTOR

Document Number: MQ081K0VP
Preliminary Datasheet V1.0

1000W, 50V High Power RF LDMOS FETs

MQ081K0VP



Description

The MQ081K00VP is a 1000-watt capable, high performance, internally matched LDMOS FET, designed for narrow band pulsed applications with frequencies 400MHz to 800MHz.

- Typical Performance (on innogration demo with device soldered):

Frequency:440MHz,: Vds = 50 Volts, Idq = 100 mA, TA = 25 C

Pulse condition	Gp (dB)	P_{OUT}(W)	η_D@P_{OUT} (%)
pulse width 100us duty cycle 10%	19.3	1060	68.5

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Internally Matched for Ease of Use
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Excellent thermal stability, low HCI drift
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	115	Vdc
Gate--Source Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+55	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case,Case Temperature 80°C, 1000W Pout, Pulse width: 100us, duty cycle: 10%, Vds=50 V, I_{DQ} = 100 mA , Frequency at 800MHz	$R_{\theta JC}$	0.02	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics (TA = 25 C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DC Characteristics					
Drain-Source Breakdown Voltage (V_{GS}=0V; I_D=100uA)	V_{DSS}	115	——	——	V
Zero Gate Voltage Drain Leakage Current	I_{DSS}	——	——	10	μA

(V_{DS} = 50 V, V_{GS} = 0 V)					
Gate--Source Leakage Current (V_{GS} = 6 V, V_{DS} = 0 V)	I_{GSS}	———	———	1	μA
Gate Threshold Voltage (V_{DS} = 50V, I_D = 600 uA)	$V_{GS}(th)$	———	1.6	———	V
Gate Quiescent Voltage (V_{DD} = 50 V, I_{DQ} = 100 mA, Measured in Functional Test)	$V_{GS(Q)}$		3.0		V

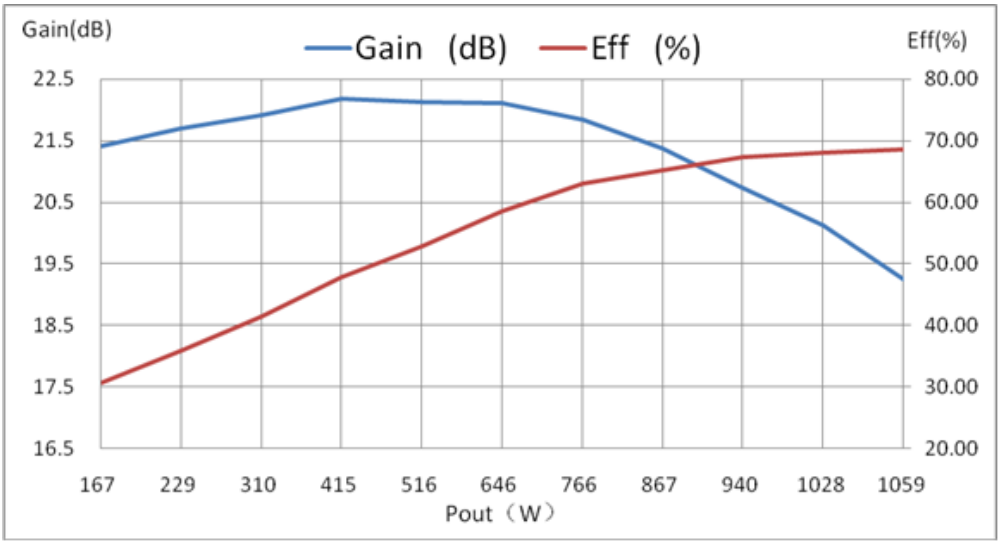
Functional Tests (In Innogration test fixture, 50 ohm system) :V_{DD} = 50 Vdc, I_{DQ} = 100 mA, f = 440MHz, Pulse CW Signal Measurements.

(Pulse Width=100 μs, Duty cycle=10%).

Power Gain @ P_{OUT}=1060W	Gp	———	19.3	———	dB
Output Power	P_{out}	———	1060	———	W
Drain Efficiency@Pout	η_D	———	68.5	———	%
Input Return Loss	IRL	———	-7	———	dB

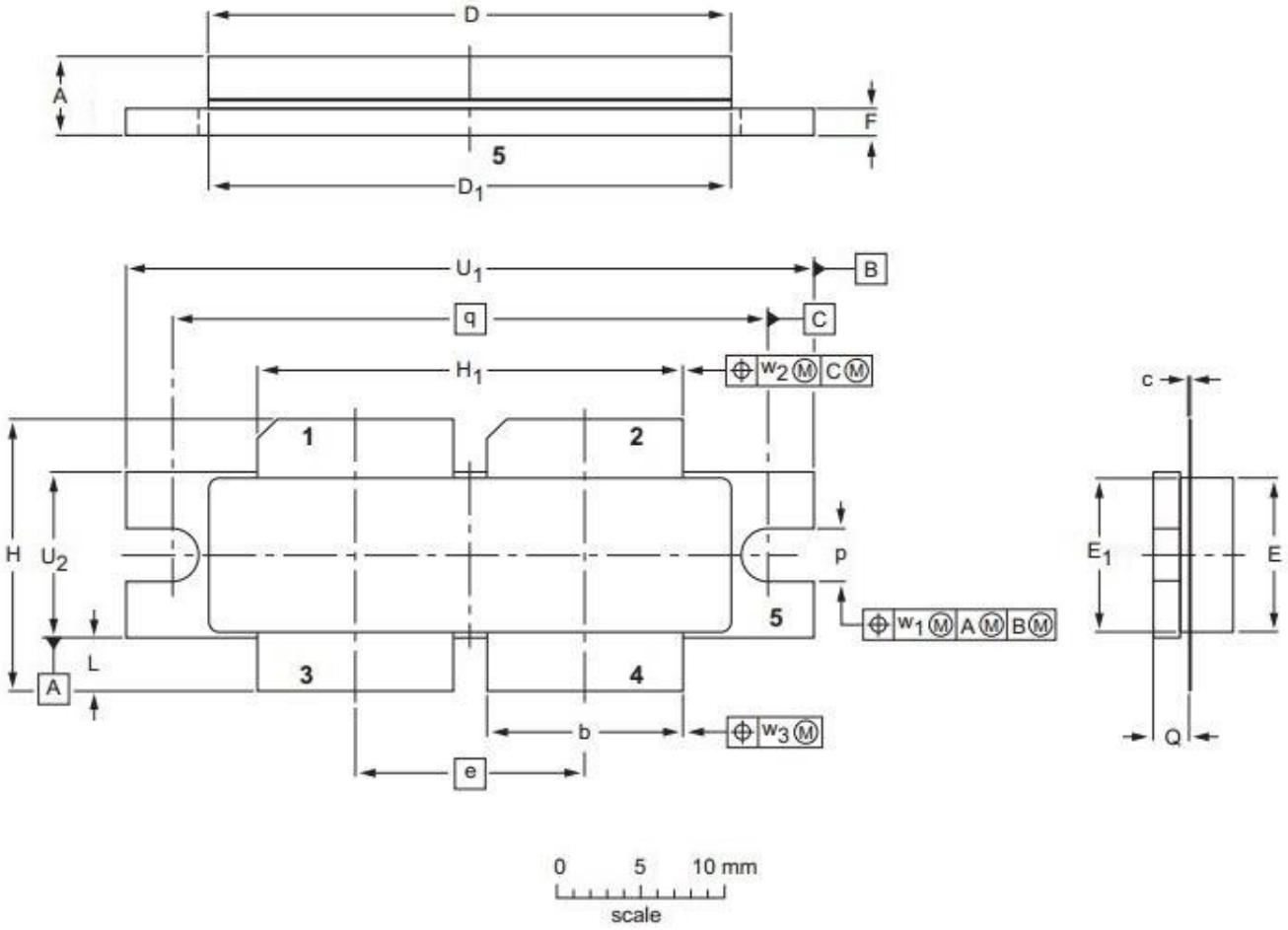
Figure 1: 440MHz Pulsed CW gain and efficiency as a Function of Output Power

Pulse width 100us and duty cycle 10%



Package Outline

Flanged ceramic package; 2 mounting holes; 4 leads（1、2—DRAIN、3、4—GATE、5—SOURCE）



UNIT	A	b	c	D	D_1	e	E	E_1	F	H	H_1	L	p	Q	q	U_1	U_2	W_1	W_2	W_2
mm	4.7 4.2	11.81 11.56	0.18 0.10	31.55 30.94	31.52 30.96	13.72	9.50 9.30	9.53 9.27	1.75 1.50	17.12 16.10	25.53 25.27	3.48 2.97	3.30 3.05	2.26 2.01	35.56	41.28 41.02	10.29 10.03	0.25	0.51	0.25
inches	0.185 0.165	0.465 0.455	0.007 0.004	1.242 1.218	1.241 1.219	0.540	0.374 0.366	0.375 0.365	0.069 0.059	0.674 0.634	1.005 0.995	0.137 0.117	0.130 0.120	0.089 0.079	1.400	1.625 1.615	0.405 0.395	0.01	0.02	0.01

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-D4E					03/12/2013

Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2017/11/14	Rev 1.0	Preliminary Datasheet Creation

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